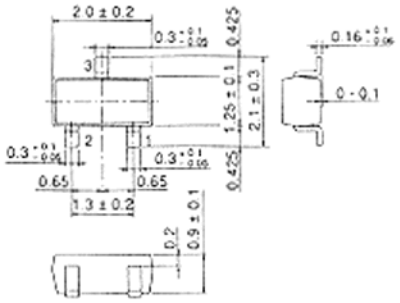
HITACHI

2SC4261

SILICON NPN EPITAXIAL

UHF LOCAL OSCILLATOR



1. Emitter
2. Base
3. Collector

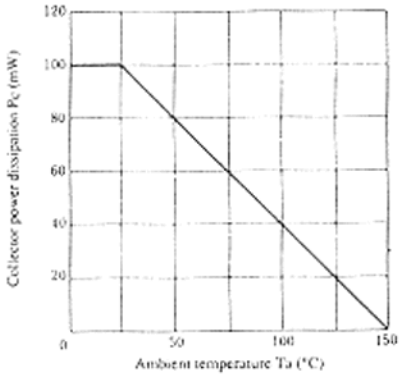
(Dimensions in mm)

(CMPAK)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC4261	Unit
Collector to base voltage	V_{CBO}	25	V
Collector to emitter voltage	V_{CEO}	15	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = 10μA, I_E = 0	25	—	—	V
Collector cutoff current	I_{CBO}	V_{CB} = 15V, I_E = 0	—	—	0.3	μA
	I_{CEO}	V_{CE} = 15V, R_{BE} = ∞	—	—	10	μA
Emitter cutoff current	I_{EBO}	V_{EB} = 3V, I_C = 0	—	—	1.0	μA
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = 20mA, I_B = 4mA	—	—	0.3	V
DC current transfer ratio	h_{FE}	V_{CE} = 5V, I_C = 5mA	50	—	180	
Collector output capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	—	0.7	1.0	pF
Gain bandwidth product	f_T	V_{CE} = 5V, I_C = 20mA	1.8	2.4	—	GHz
Oscillating output voltage	V_{OSC}	V_{CC} = 5V, I_C = 5mA, f = 930MHz	—	200	—	mV

* Marking is [QI–].

■ See characteristic curves of 2SC4196.